IN THE CLAIMS:

1-24. (Withdrawn)

25-49. (Canceled)

50. (Currently Amended) A method of manufacturing a device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode connecting the wiring with the thin film transistor, over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode, and the interlayer insulating film;

forming a protective film over the resin insulating film;

after forming the protective film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

after moving the substrate, removing the protective film;

etching the resin insulating film to expose said pixel electrode;

forming a light emitting layer over said pixel electrode after said etching, wherein said steps of removing, etching and forming a light emitting layer are performed in said second processing room.

51. (Previously presented) A method of manufacturing a device according to claim 50, wherein the pixel electrode is an anode or a cathode.

52. (Previously presented) A method of manufacturing a device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating

surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode connecting the wiring with the thin film transistor, over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode and the interlayer insulating film;

forming a protective film for preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

removing the protective film;

etching the resin insulating film to expose said pixel electrode;

forming a light emitting layer over said pixel electrode.

53. (Previously presented) A method of manufacturing a device according to claim 52, wherein the pixel electrode is an anode or a cathode.

54. (Previously presented) A method of manufacturing a device according to claim 52, wherein the protective film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkylmonoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl ether.

55. (Previously presented) A method of manufacturing a device according to claim 54, wherein the protective film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material is formed by spin coating or

evaporation.

56. (Previously presented) A method of manufacturing a device according to claim 52, wherein the protective film for preventing the substrate from contamination and electrostatic discharge damage comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

57. (Previously presented) A method of manufacturing a device according to claim 53, wherein the method further comprises the steps of wiping the pixel electrode, forming an organic compound layer over the pixel electrode.

58-61. (Canceled)

62. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode connecting to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode and the interlayer insulating film; and

forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room,

after moving the substrate, removing the film;

etching the resin insulating film to expose said pixel electrode;

forming a light emitting layer over said pixel electrode after said etching, wherein said steps of removing, etching and forming a light emitting layer are performed in said second processing room.

63. (Previously presented) A method of manufacturing a light emitting device according to claim 62, wherein the film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

64. (Previously presented) A method of manufacturing a light emitting device according to claim 62, wherein the film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

65. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode connecting to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode, and the interlayer insulating film;

forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

after moving the substrate, removing the film;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the first electrode;

forming a second electrode on the organic compound layer.

66. (Previously presented) A method of manufacturing a light emitting device according to claim 65, wherein the film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

67. (Previously presented) A method of manufacturing a light emitting device according to claim 65, wherein the film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

68. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode connecting the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode and the interlayer insulating film;

after forming the resin insulating film over the wiring, the pixel electrode and the interlayer insulating film, forming a film comprising an organic conductive material over the

resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage,

wherein the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film.

69. (Previously presented) A method of manufacturing a light emitting device according to claim 68, wherein the organic conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,
alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

70. (Previously presented) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode connecting to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode, and the interlayer insulating film; and

after forming the resin insulating film over, the wiring, the pixel electrode, and the interlayer insulating film, forming a film comprising an organic conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film comprising the organic conductive material, moving the substrate over which the thin film transistor is formed from a first processing room to a

second processing room.

71. (Previously presented) A method of manufacturing a light emitting device according to claim 70, wherein the organic conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,
alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

72. (Currently amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a first electrode connecting to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the first electrode, and the interlayer insulating film;

after forming the resin insulating film over, the wiring, the first electrode, and the interlayer insulating film, forming a film comprising an organic conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film comprising the organic conductive material, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

<u>after moving the substrate,</u> removing the film;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the first electrode;

forming a second electrode on the organic compound layer.

73. (Previously presented) A method of manufacturing a light emitting device according to claim 72, wherein the organic conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,
alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

74. (Currently amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode connecting the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode, and the interlayer insulating film;

forming a film comprising an organic insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage,

<u>wherein the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film</u>.

75. (Previously presented) A method of manufacturing a light emitting

device according to claim 74, wherein the organic insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

76. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode connecting to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode, and the interlayer insulating film; and

forming a film comprising an organic insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

77. (Previously presented) A method of manufacturing a light emitting device according to claim 76, wherein the organic insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

78. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a first electrode connecting to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the first electrode, and the interlayer insulating film;

forming a film comprising an organic insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

after moving the substrate, removing the film;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the first electrode;

forming a second electrode on the organic compound layer.

79. (Previously presented) A method of manufacturing a light emitting device according to claim 78, wherein the organic insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

80. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

performing plasma treatment on a surface of the interlayer insulating film;

forming a contact hole in the interlayer insulating film after performing the plasma treatment;

forming a wiring over the interlayer insulating film;

forming a pixel electrode connecting to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode, and the interlayer insulating film; and

forming a film over the resin insulating film, the film preventing the substrate

over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

81. (Previously presented) A method of manufacturing a light emitting device according to claim 80, wherein the film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylam monium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

82. (Previously presented) A method of manufacturing a light emitting device according to claim 80, wherein the film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

83. (New) A method of manufacturing a light emitting device according to claim 50, wherein in the step of forming the protective film, the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film.

84. (New) A method of manufacturing a light emitting device according to claim 52, wherein in the step of forming the protective film, the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film.

85. (New) A method of manufacturing a light emitting device according to claim 62, wherein in the step of forming the film, the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film.

86. (New) A method of manufacturing a light emitting device according to claim 65, wherein in the step of forming the film, the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film.

87. (New) A method of manufacturing a light emitting device according to claim 70, wherein in the step of forming the film, the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film.

88. (New) A method of manufacturing a light emitting device according to claim 72, wherein in the step of forming the film, the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film.

89. (New) A method of manufacturing a light emitting device according to claim 76, wherein in the step of forming the film, the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film.

90. (New) A method of manufacturing a light emitting device according to claim 78, wherein in the step of forming the film, the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film.

91. (New) A method of manufacturing a light emitting device according to claim 80, wherein in the step of forming the film, the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film.